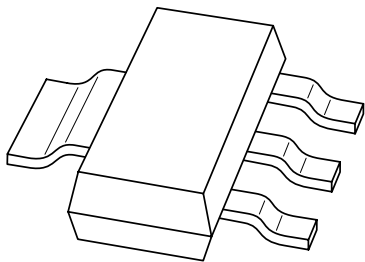


# DATA SHEET



## **BSP122**

**N-channel enhancement mode  
vertical D-MOS transistor**

Product specification  
Supersedes data of 1997 Jun 23

2001 May 18

# N-channel enhancement mode vertical D-MOS transistor

**BSP122**

## FEATURES

- Direct interface to C-MOS, TTL, etc.
- High-speed switching
- No secondary breakdown.

## DESCRIPTION

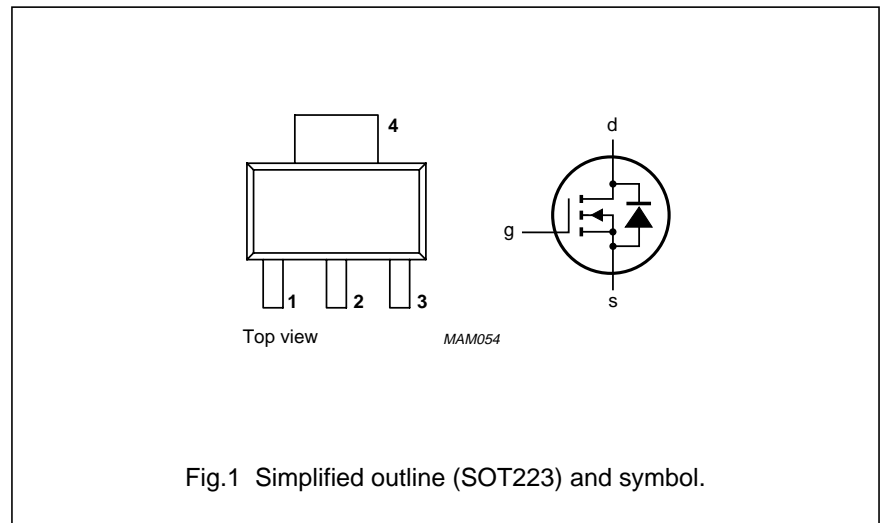
N-channel enhancement mode vertical D-MOS transistor in a SOT223 package and intended for use as a line current interruptor in telephone sets and for applications in relay, high-speed and line transformer drivers.

## PINNING - SOT223

PIN	DESCRIPTION
1	gate
2	drain
3	source
4	drain

## QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	UNIT
$V_{DS}$	drain-source voltage (DC)	200	V
$I_D$	drain current (DC)	550	mA
$R_{DSon}$	drain-source on-state resistance	2.5	$\Omega$
$V_{GSth}$	gate-source threshold voltage	2	V



## LIMITING VALUES

In accordance with the Absolute Maximum System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$V_{DS}$	drain-source voltage (DC)		–	200	V
$V_{GSO}$	gate-source voltage (DC)	open drain	–	$\pm 20$	V
$I_D$	drain current (DC)		–	550	mA
$I_{DM}$	peak drain current		–	3	A
$P_{tot}$	total power dissipation	$T_{amb} \leq 25\text{ }^\circ\text{C}$ ; note 1	–	1.5	W
$T_{stg}$	storage temperature		–55	+150	$^\circ\text{C}$
$T_j$	junction temperature		–	150	$^\circ\text{C}$

## Note

1. Transistor mounted on an epoxy printed circuit board, 40 x 40 x 1.5 mm, mounting pad for the drain tab minimum 6 cm<sup>2</sup>.

## THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
$R_{th\ j-a}$	thermal resistance from junction to ambient; note 1	83.3	K/W

## Note

1. Transistor mounted on an epoxy printed circuit board, 40 x 40 x 1.5 mm, mounting pad for the drain tab minimum 6 cm<sup>2</sup>.

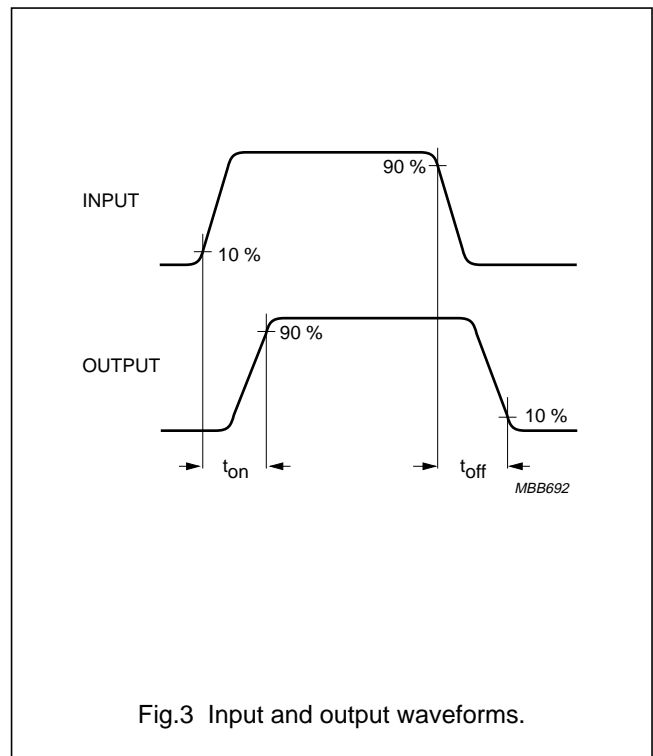
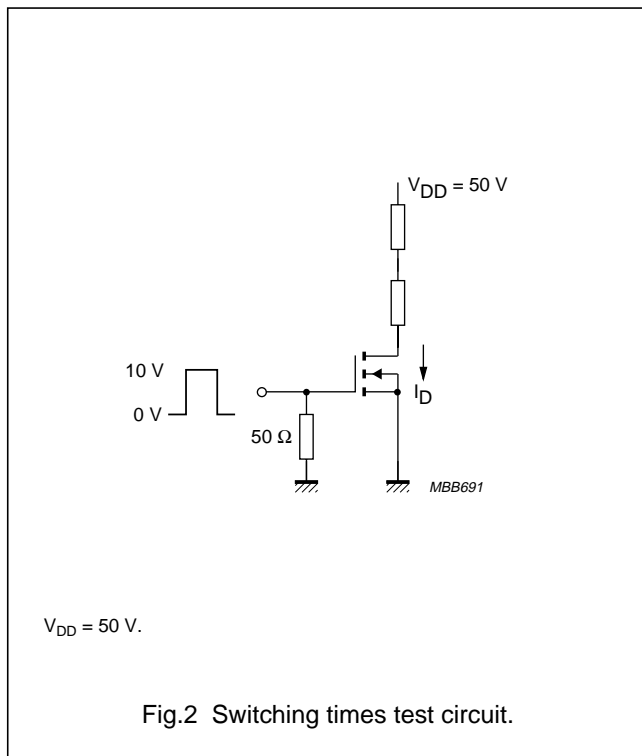
# N-channel enhancement mode vertical D-MOS transistor

BSP122

## CHARACTERISTICS

T<sub>j</sub> = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	I <sub>D</sub> = 10 μA; V <sub>GS</sub> = 0	200	–	–	V
I <sub>DSS</sub>	drain-source leakage current	V <sub>DS</sub> = 160 V; V <sub>GS</sub> = 0	–	–	1	μA
I <sub>GSS</sub>	gate-source leakage current	V <sub>GS</sub> = ±20 V; V <sub>DS</sub> = 0	–	–	100	nA
V <sub>GSth</sub>	gate-source threshold voltage	I <sub>D</sub> = 1 mA; V <sub>GS</sub> = V <sub>DS</sub>	0.4	–	2	V
R <sub>DSon</sub>	drain-source on-resistance	I <sub>D</sub> = 750 mA; V <sub>GS</sub> = 10 V	–	1.7	2.5	Ω
		I <sub>D</sub> = 20 mA; V <sub>GS</sub> = 2.4 V	–	3	–	Ω
Y <sub>fs</sub>	transfer admittance	I <sub>D</sub> = 750 mA; V <sub>DS</sub> = 25 V	400	900	–	mS
C <sub>iSS</sub>	input capacitance	V <sub>DS</sub> = 25 V; V <sub>GS</sub> = 0; f = 1 MHz	–	100	–	pF
C <sub>oSS</sub>	output capacitance	V <sub>DS</sub> = 25 V; V <sub>GS</sub> = 0; f = 1 MHz	–	20	–	pF
C <sub>rSS</sub>	reverse transfer capacitance	V <sub>DS</sub> = 25 V; V <sub>GS</sub> = 0; f = 1 MHz	–	10	–	pF
<b>Switching times (see Figs 2 and 3)</b>						
t <sub>on</sub>	turn-on time	I <sub>D</sub> = 750 mA; V <sub>DD</sub> = 50 V; V <sub>GS</sub> = 0 to 10 V	–	10	20	ns
t <sub>off</sub>	turn-off time	I <sub>D</sub> = 750 mA; V <sub>DD</sub> = 50 V; V <sub>GS</sub> = 0 to 10 V	–	45	60	ns



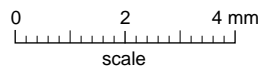
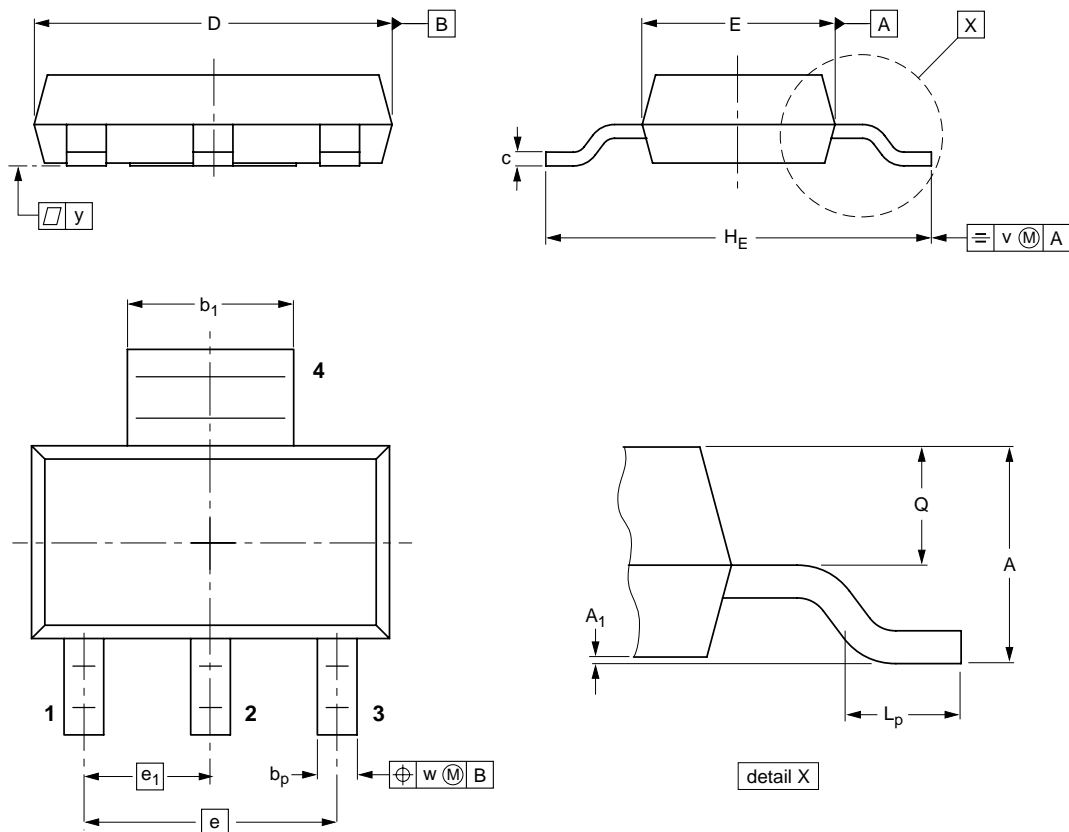
N-channel enhancement mode  
vertical D-MOS transistor

BSP122

PACKAGE OUTLINE

Plastic surface mounted package; collector pad for good heat transfer; 4 leads

SOT223



DIMENSIONS (mm are the original dimensions)

UNIT	A	A <sub>1</sub>	b <sub>p</sub>	b <sub>1</sub>	c	D	E	e	e <sub>1</sub>	H <sub>E</sub>	L <sub>p</sub>	Q	v	w	y
mm	1.8 1.5	0.10 0.01	0.80 0.60	3.1 2.9	0.32 0.22	6.7 6.3	3.7 3.3	4.6	2.3	7.3 6.7	1.1 0.7	0.95 0.85	0.2	0.1	0.1

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT223			SC-73			97-02-28 99-09-13

# N-channel enhancement mode vertical D-MOS transistor

BSP122

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DATA SHEET STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)</sup>	DEFINITIONS
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N-channel enhancement mode  
vertical D-MOS transistor

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**NOTES**

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N-channel enhancement mode  
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**NOTES**

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